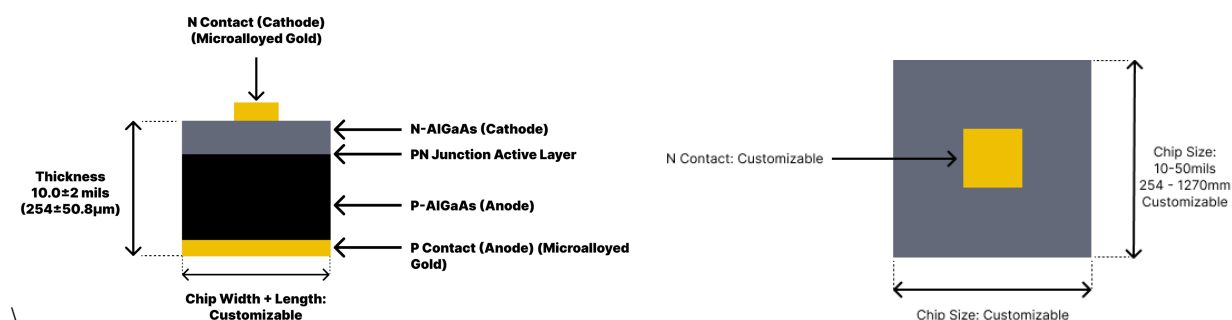


MANULED Infrared LED Bare Die Chip**2025**

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, DDH	N (cathode) up

**Optical and Electrical Characteristics**

Characteristics					Dimensions			Metallization	
λ_p [nm] If=20mA	Po[mW] If=20mA	Vf[V] If=20mA	Vr[V] If=10µA	Absolute Maximum Rating [mA]	Chip Size [µm]	Chip Thickness [µm] [Mils]	Top-Side	Top Contact (Cathode)	Bottom Contact (Anode)
850	1.0 - 2.2	1.0 - 1.8	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
860	1.0 - 2.2	1.0 - 1.8	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
870	1.0 - 2.2	1.0 - 1.8	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
880	1.0 - 2.2	1.0 - 1.8	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
890	1.0 - 2.2	1.0 - 1.8	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
900	1.0 - 2.2	1.0 - 1.6	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
910	1.0 - 2.2	1.0 - 1.6	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
920	1.0 - 2.2	1.0 - 1.6	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
930	1.0 - 2.2	1.0 - 1.6	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.
940	1.0 - 2.2	1.0 - 1.6	5	80	Customizable	254±50 µm 10±2 Mils	N Cathode	14000 Å MIN. Au.	8000 Å MIN. Au.

 Note: Each row above represents a separate LED chip designed for a specific peak emission wavelength. Chips do not emit uniformly across the 850–940 nm range.

Packing

Chips on adhesive film with wire bond side up

Pricing

Unit Price (<1M): Starting from \$0.10, Unit Price (≥1M): Starting from \$0.7



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.